

# High Power Infrared Emitter (850 nm)

## Version 1.4

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### SFH 4556



#### Features:

- High Power Infrared LED
- Short switching time

#### Applications

- Infrared Illumination for cameras
- Sensor technology
- Data transmission

#### Notes

Depending on the mode of operation, these devices emit highly concentrated non visible infrared light which can be hazardous to the human eye. Products which incorporate these devices have to follow the safety precautions given in IEC 60825-1 and IEC 62471.

#### Ordering Information

| Type:        | Radiant Intensity<br>$I_e$ [mW/sr]<br>$I_F= 100 \text{ mA}, t_p= 20 \text{ ms}$ | Ordering Code |
|--------------|---|---------------|
| SFH 4556     | 145 ( $\geq 63$ )   | Q65110A6087   |
| SFH 4556-AW  | 100 ... 200   | Q65111A9676   |
| SFH 4556-VAW | 63 ... 200  | Q65110A9803   |

Note: Measured at a solid angle of  $\Omega = 0.01 \text{ sr}$

**Maximum Ratings** ( $T_A = 25\text{ °C}$ )

| Parameter   | Symbol            | Values      | Unit  |
|---|-------------------|-------------|-------|
| Operation and storage temperature range                           | $T_{op}; T_{stg}$ | -40 ... 100 | °C    |
| Reverse voltage   | $V_R$             | 5           | V     |
| Forward current   | $I_F$             | 100         | mA    |
| Surge current<br>( $t_p \leq 100\ \mu\text{s}$ , $D = 0$ )        | $I_{FSM}$         | 1           | A     |
| Power consumption   | $P_{tot}$         | 180         | mW    |
| ESD withstand voltage<br>(acc. to ANSI/ ESDA/ JEDEC JS-001 - HBM) | $V_{ESD}$         | 2           | kV    |
| Thermal resistance junction - ambient <sup>1) page 8</sup>        | $R_{thJA}$        | 450         | K / W |

**Characteristics** ( $T_A = 25\text{ °C}$ )

| Parameter  |             | Symbol               | Values                             | Unit          |
|--|-------------|----------------------|------------------------------------|---------------|
| Peak wavelength<br>( $I_F = 100\text{ mA}$ , $t_p = 20\text{ ms}$ )  | (typ)       | $\lambda_{peak}$     | 860                                | nm            |
| Centroid wavelength<br>( $I_F = 100\text{ mA}$ , $t_p = 20\text{ ms}$ )                                      | (typ)       | $\lambda_{centroid}$ | 850                                | nm            |
| Spectral bandwidth at 50% of $I_{max}$<br>( $I_F = 100\text{ mA}$ , $t_p = 20\text{ ms}$ )                   | (typ)       | $\Delta\lambda$      | 30                                 | nm            |
| Half angle   | (typ)       | $\varphi$            | $\pm 20$                           | °             |
| Dimensions of active chip area   | (typ)       | L x W                | 0.3 x 0.3                          | mm x mm       |
| Rise and fall time of $I_e$ ( 10% and 90% of $I_{e,max}$ )<br>( $I_F = 100\text{ mA}$ , $R_L = 50\ \Omega$ ) | (typ)       | $t_r, t_f$           | 12                                 | ns            |
| Forward voltage<br>( $I_F = 100\text{ mA}$ , $t_p = 20\text{ ms}$ )  | (typ (max)) | $V_F$                | 1.5 ( $\leq 1.8$ )                 | V             |
| Forward voltage<br>( $I_F = 1\text{ A}$ , $t_p = 100\ \mu\text{s}$ )   | (typ (max)) | $V_F$                | 2.4 ( $\leq 3$ )                   | V             |
| Reverse current<br>( $V_R = 5\text{ V}$ )  |             | $I_R$                | not designed for reverse operation | $\mu\text{A}$ |
| Total radiant flux<br>( $I_F = 100\text{ mA}$ , $t_p = 20\text{ ms}$ )                                       | (typ)       | $\Phi_e$             | 60                                 | mW            |
| Temperature coefficient of $I_e$ or $\Phi_e$<br>( $I_F = 100\text{ mA}$ , $t_p = 20\text{ ms}$ )             | (typ)       | $TC_I$               | -0.5                               | % / K         |
| Temperature coefficient of $V_F$<br>( $I_F = 100\text{ mA}$ , $t_p = 20\text{ ms}$ )                         | (typ)       | $TC_V$               | -0.7                               | mV / K        |
| Temperature coefficient of wavelength<br>( $I_F = 100\text{ mA}$ , $t_p = 20\text{ ms}$ )                    | (typ)       | $TC_\lambda$         | 0.3                                | nm / K        |

Grouping ( $T_A = 25\text{ °C}$ )

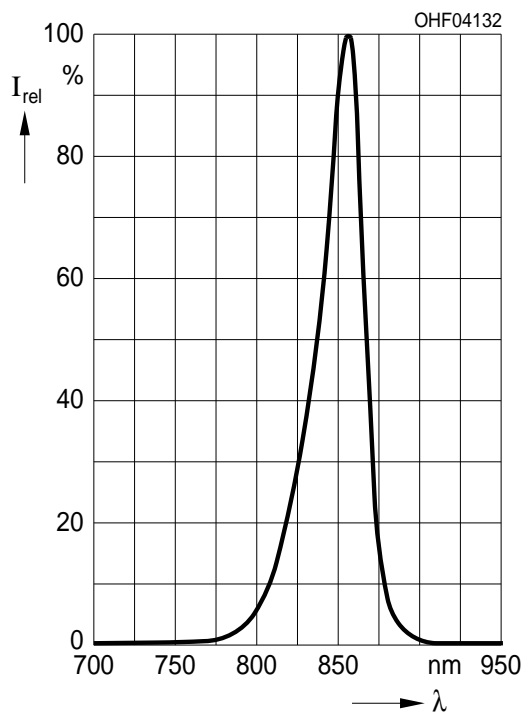
| Group       | Min Radiant Intensity<br>$I_F = 100\text{ mA}, t_p = 20\text{ ms}$<br>$I_{e, \min}$ [mW / sr] | Max Radiant Intensity<br>$I_F = 100\text{ mA}, t_p = 20\text{ ms}$<br>$I_{e, \max}$ [mW / sr] | Typ Radiant Intensity<br>$I_F = 1\text{ A}, t_p = 25\text{ }\mu\text{s}$<br>$I_{e, \text{typ}}$ [mW / sr] |
|-------------|---|---|---|
| SFH 4556-V  | 63  | 125   | 750   |
| SFH 4556-AW | 100   | 200   | 1200  |
| SFH 4556-BW | 160   | 320   | 1900  |

Note: measured at a solid angle of  $\Omega = 0.01\text{ sr}$

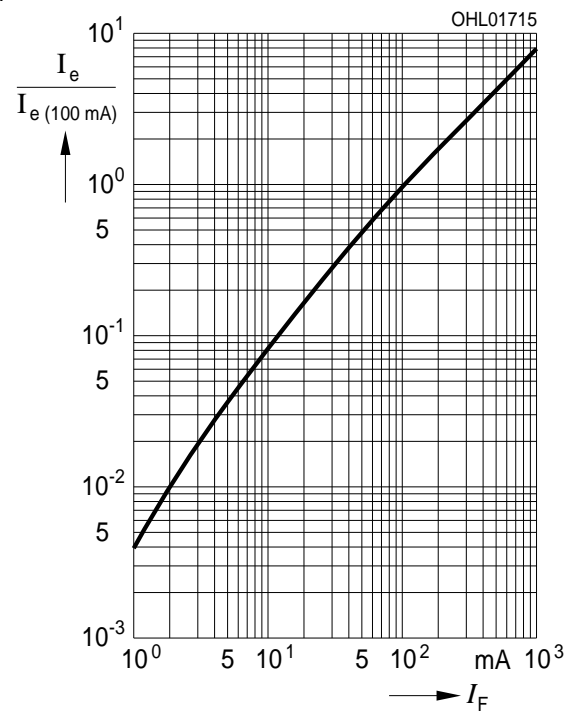
Only one group in one packing unit (variation lower 2:1).

Relative Spectral Emission <sup>2) page 8</sup>

$$I_{\text{rel}} = f(\lambda), T_A = 25\text{ °C}$$

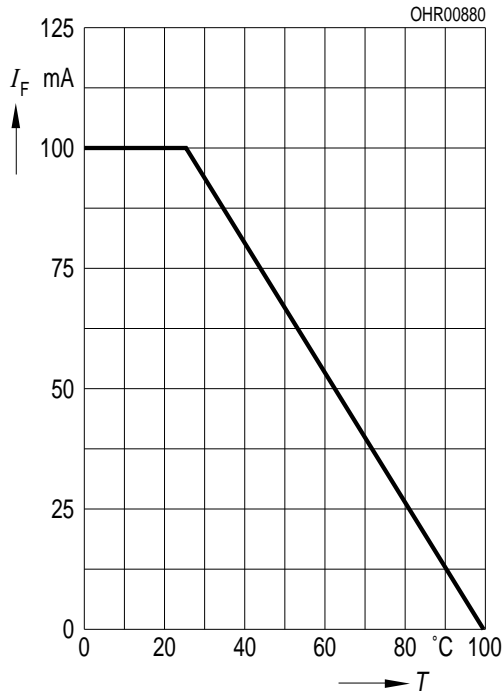
Radiant Intensity <sup>2) page 8</sup>

$$I_e / I_e(100\text{ mA}) = f(I_F), \text{ single pulse, } t_p = 25\text{ }\mu\text{s}, T_A = 25\text{ °C}$$



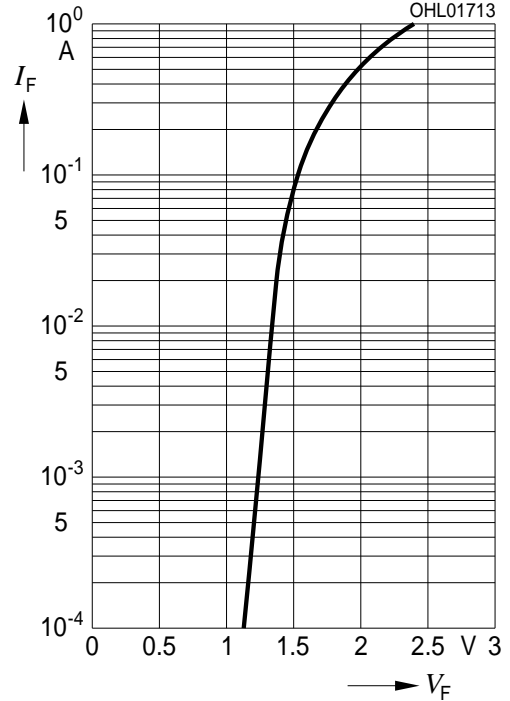
**Max. Permissible Forward Current**

$I_F = f(T_A), R_{thJA} = 450 \text{ K/W}$



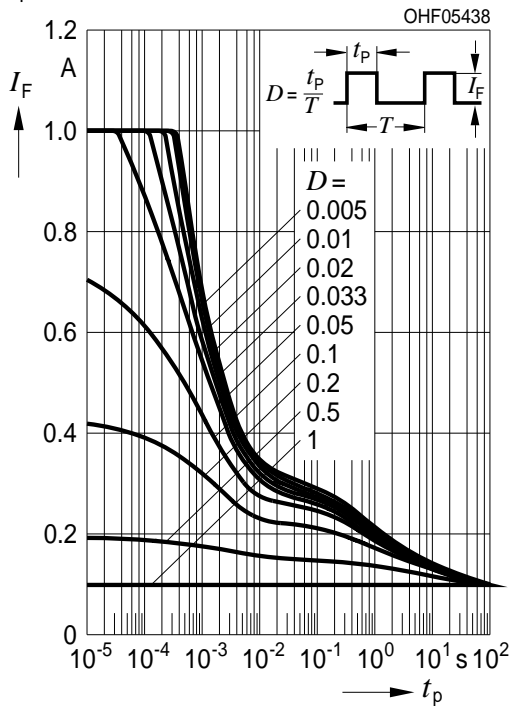
**Forward Current** <sup>2) page 8</sup>

$I_F = f(V_F), \text{ single pulse, } t_p = 100 \mu\text{s}, T_A = 25^\circ\text{C}$



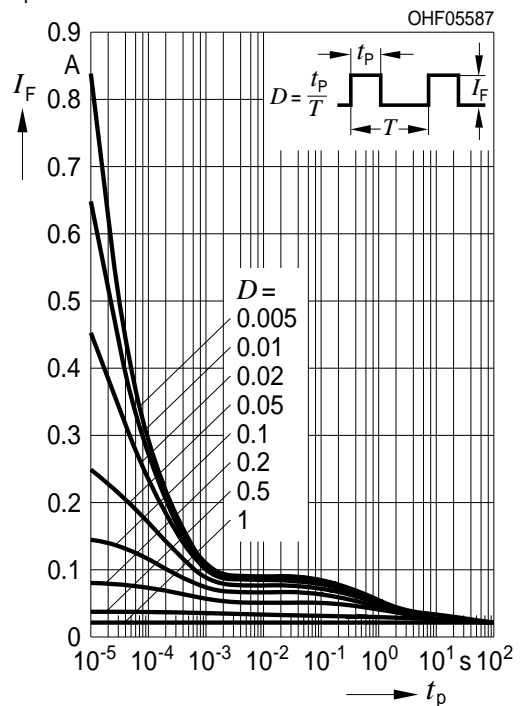
**Permissible Pulse Handling Capability**

$I_F = f(t_p), T_A = 25^\circ\text{C}, \text{ duty cycle } D = \text{parameter}$



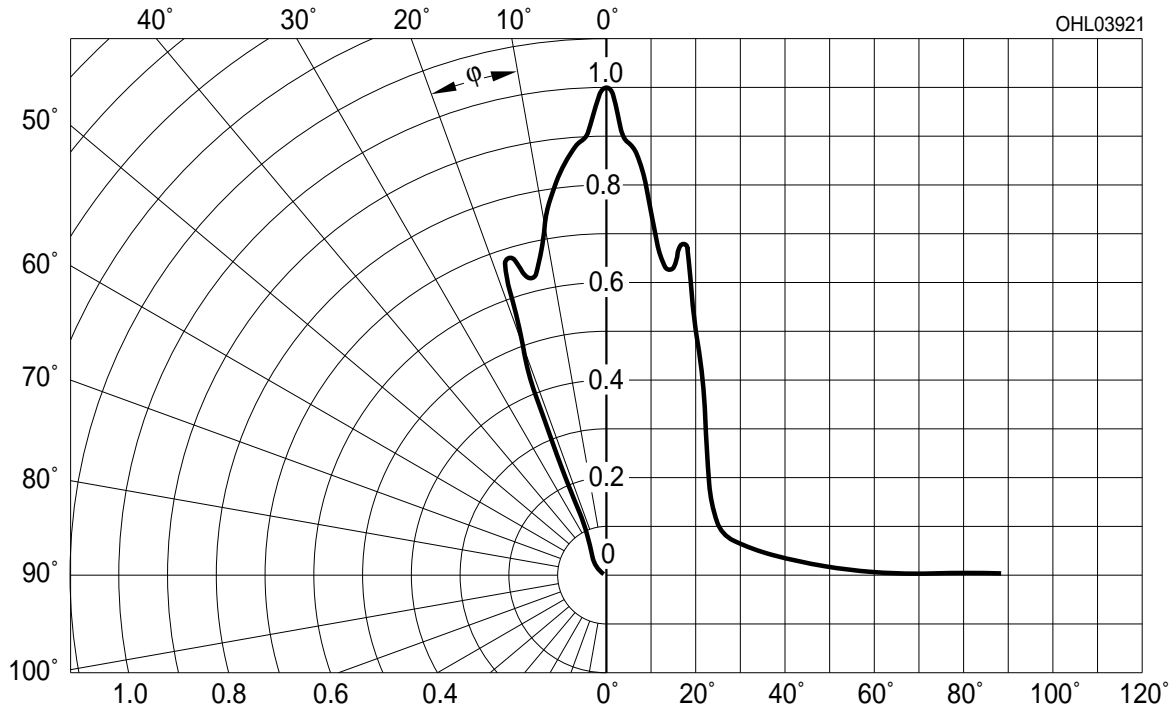
**Permissible Pulse Handling Capability**

$I_F = f(t_p), T_A = 85^\circ\text{C}, \text{ duty cycle } D = \text{parameter}$

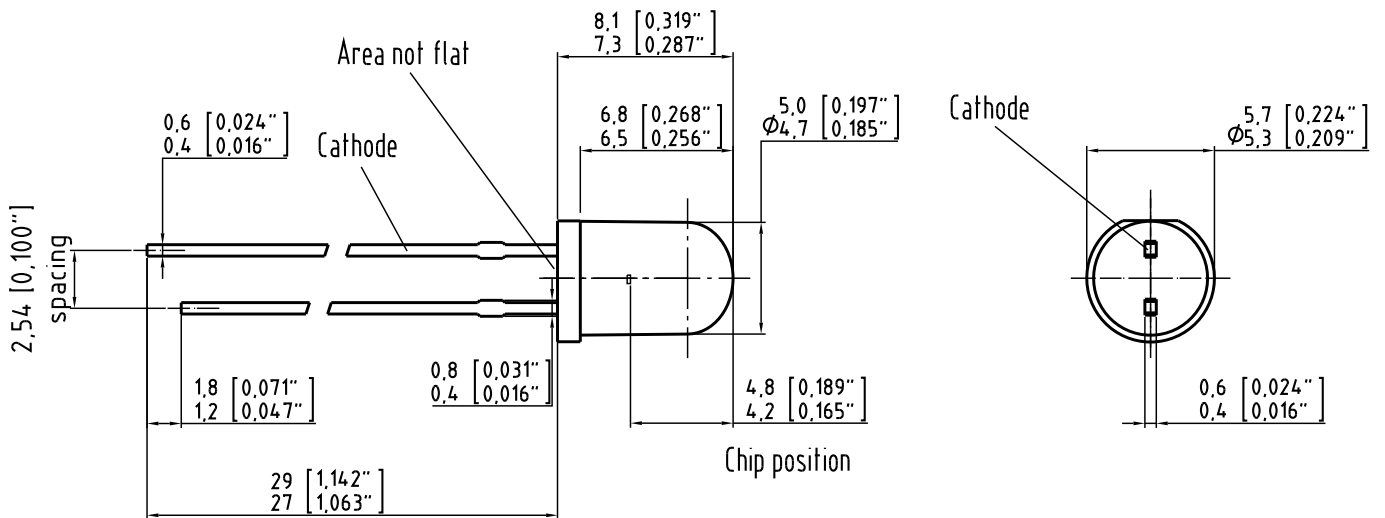


**Radiation Characteristics** <sup>2) page 8</sup>

$I_{rel} = f(\phi), T_A = 25^\circ C$



**Package Outline**



C63062-A3930-A1-02

*Dimensions in mm (inch).*

**Package**

5mm Radial (T 1 3/4), Epoxy

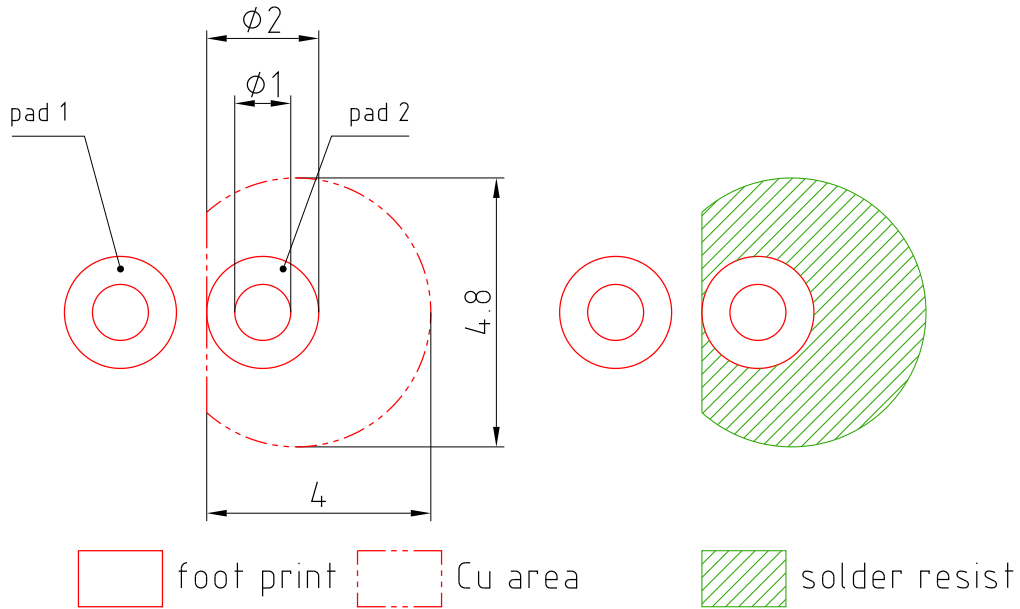
**Approximate Weight:**

0.3 g

**Note**

Packing information is available on the internet (online product catalog).

**Recommended Solder Pad**



E062.3010.188-01

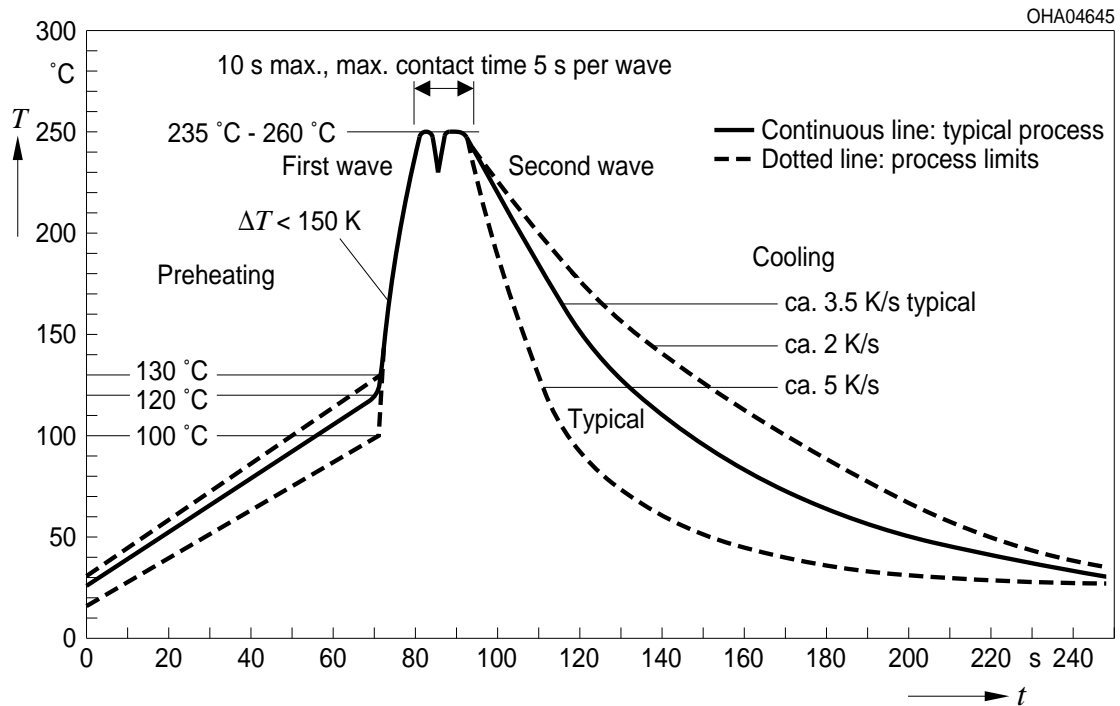
Dimensions in mm.

**Note:**

pad 1: cathode

**TTW Soldering**

IEC-61760-1 TTW

**Disclaimer**

Language english will prevail in case of any discrepancies or deviations between the two language wordings.

**Attention please!**

The information describes the type of component and shall not be considered as assured characteristics.

Terms of delivery and rights to change design reserved. Due to technical requirements components may contain dangerous substances.

For information on the types in question please contact our Sales Organization.

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\*\*) Life support devices or systems are intended (a) to be implanted in the human body, or (b) to support and/or maintain and sustain human life. If they fail, it is reasonable to assume that the health and the life of the user may be endangered.

**Glossary**

- 1) **Thermal resistance:** junction -ambient, mounted on PC-board (FR4), pads size 16 mm<sup>2</sup> each
- 2) **Typical Values:** Due to the special conditions of the manufacturing processes of LED, the typical data or calculated correlations of technical parameters can only reflect statistical figures. These do not necessarily correspond to the actual parameters of each single product, which could differ from the typical data and calculated correlations or the typical characteristic line. If requested, e.g. because of technical improvements, these typ. data will be changed without any further notice.



**Published by OSRAM Opto Semiconductors GmbH**  
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